

Substitute Form PTO-1449
(Modified)U.S. Department of Commerce
Patent and Trademark OfficeAttorney's Docket No.
10417-118001Application No.
10/076,154**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

Applicant
Yoshinori Hino et al.Filing Date
February 14, 2002Group Art Unit
2826**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
TT	AQ	Taiwanese Office Action dated November 1, 2002
TT	AR	Clement H. Wann, "A Comparative Study of Advanced MOSFET Concepts", <u>IEEE Transactions of Electric</u> , Volume 43, (1996)
TT	AS	"Phenomena in Graded Junction Devices"; <u>Texas Instruments Incorporated</u>
TT	AT	McGraw-Hill, "ULSI Technology", (1996)

Examiner Signature <i>tw</i>	Date Considered 08/03
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Substitute Disclosure Form (PTO-1449)